

## SOT-23 Plastic-Encapsulate Transistors

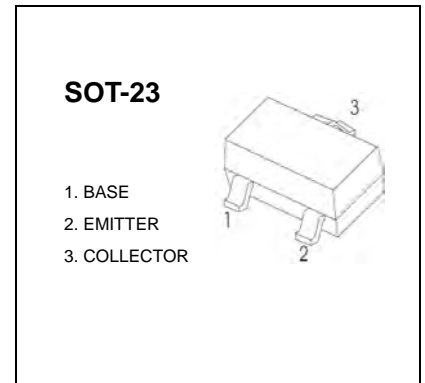
**MMBTA92** TRANSISTOR (PNP)

### FEATURES

High voltage transistor

MARKING:2D

MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$  unless otherwise noted)

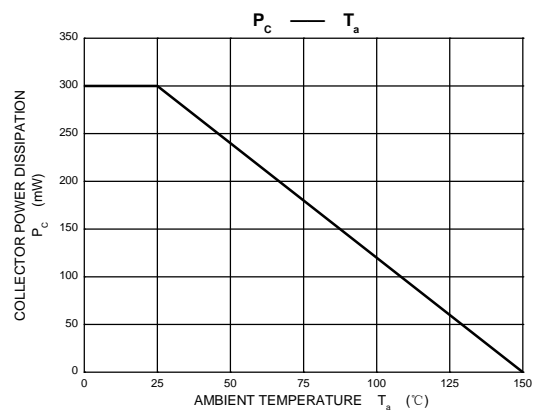
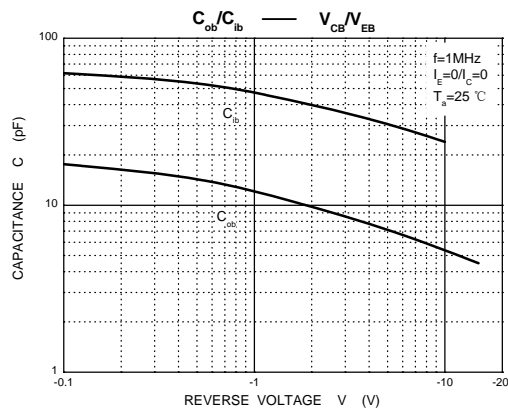
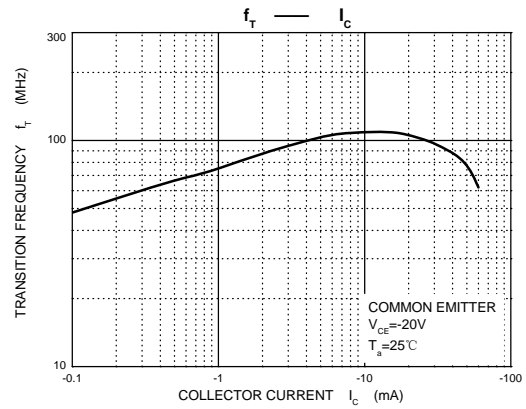
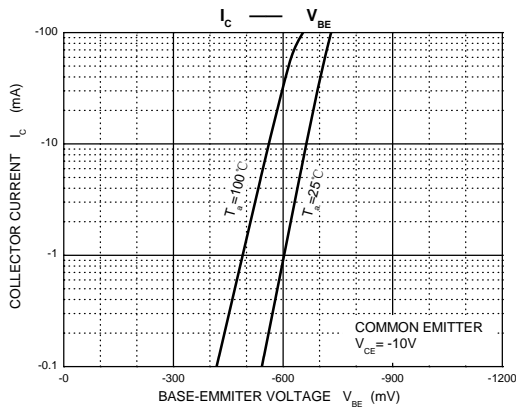
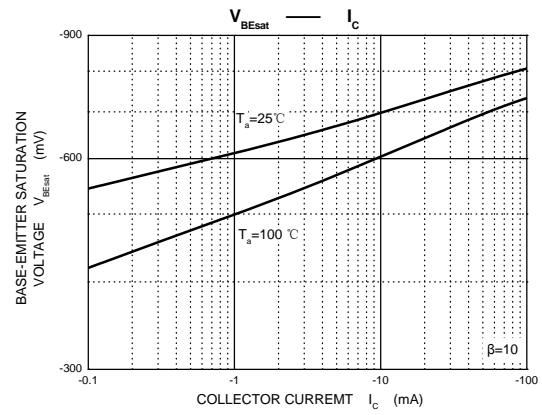
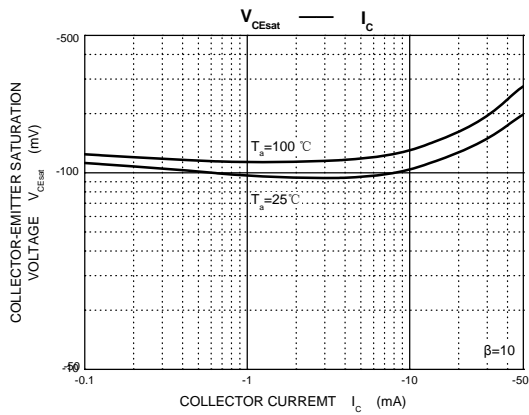
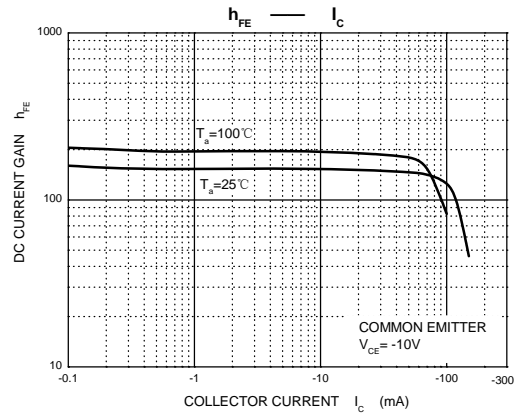
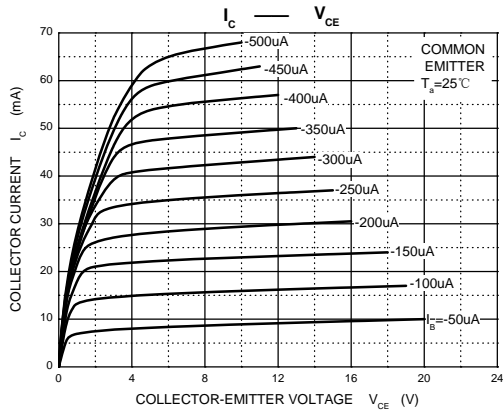


Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	-300	V
$V_{CEO}$	Collector-Emitter Voltage	-300	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-200	mA
$I_{CM}$	Collector Current -Pulsed	-500	mA
$P_C$	Collector Power Dissipation	300	mW
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	410	$^\circ\text{C}/\text{mW}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -200\text{V}, I_E = 0$		-0.25	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$		-0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	60		
	$h_{FE(2)}$	$V_{CE} = -10\text{V}, I_C = -10\text{mA}$	100	200	
	$h_{FE(3)}$	$V_{CE} = -10\text{V}, I_C = -30\text{mA}$	60		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20\text{mA}, I_B = -2\text{mA}$		-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20\text{mA}, I_B = -2\text{mA}$		-0.9	V
Transition frequency	$f_T$	$V_{CE} = -20\text{V}, I_C = -10\text{mA}$ $f = 30\text{MHz}$	50		MHz

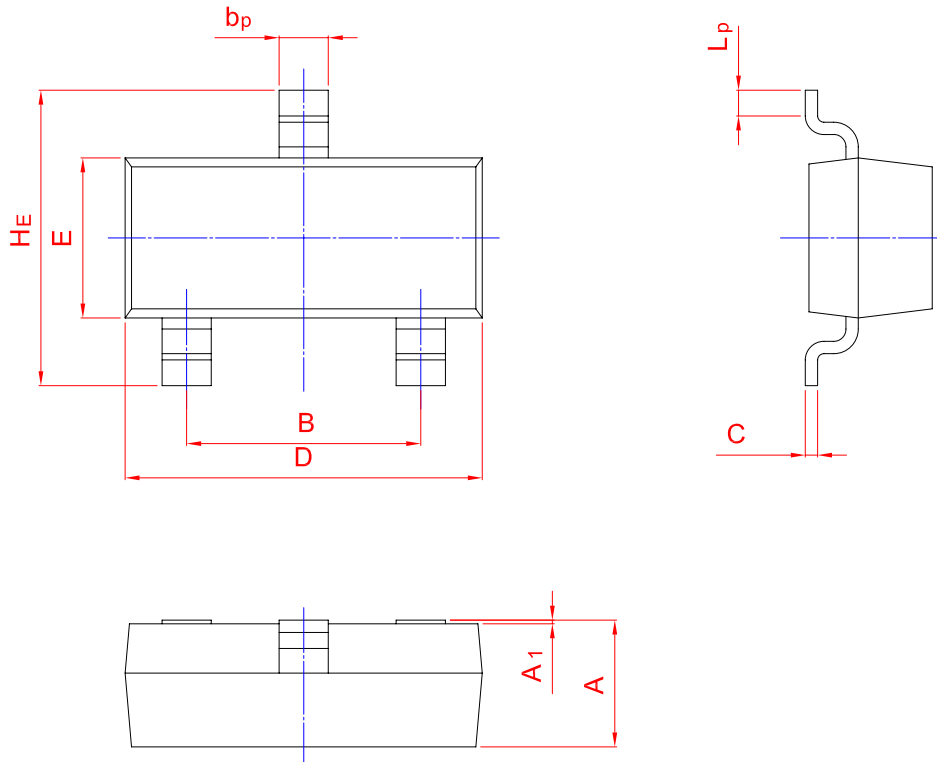
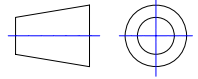
## Typical Characteristics



## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20

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